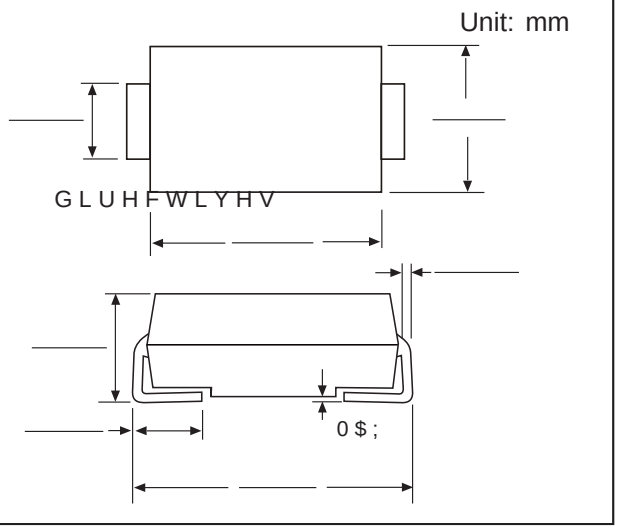
60& 3/$67,&25(&7,),(56

)($785(6

- ")RU VXUIDFH PRXQWHG DSSOLFDWLRQV
- "/RZ SURILOH SDFNDJH
- "*ODVV 3DVVLYDWHG &KLS -XQFWLRQ
- "(DV\ WR SLFN DQG SODFH
- "/HDG IUHH LQ FRPSO\ ZLWK (8 5R+6



0(&+$1,&$/ '7

- &DVH: molded plastic body over passivated chip
- 7HUPLQDOV: Plated, solderable per MIL-STD-750, Method 2026
- 3RODULW\: Color band denotes cathode end

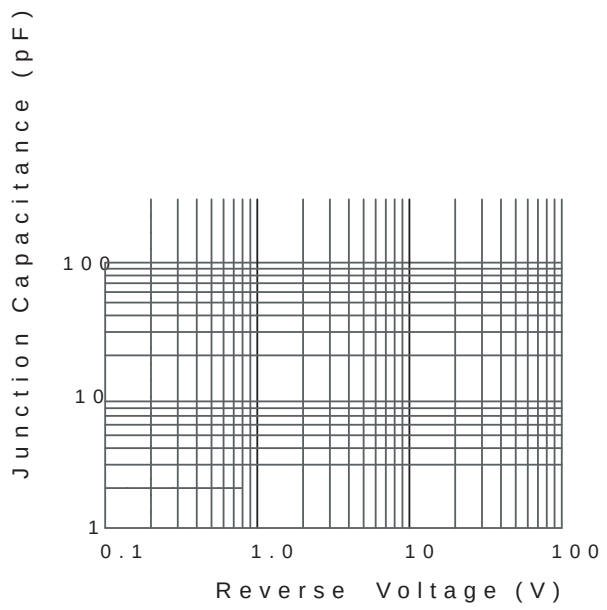
0$;,080 5$7,1*6 $1' &+$5$&7(5,67,&6

$PELHQW WHPSHUDWXUH XQOHVV RWKHUZLVH VSHFLILHG

Parameter	Symbols								Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current	$I_{F(AV)}$	5							A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load	I_{FSM}	120							A
Maximum Instantaneous Forward Voltage at 5 A	V_F	1.0							V
Maximum DC Reverse Current at Rated DC Blocking Voltage	T_a=25°C T_a=125°C	I_R	5 100						¼A
Typical Junction Capacitance		50							pF
		35 13							
Operating and Storage Temperature Range		-55 ~ +150							°

ÿ 1ÿ Measured at 1 MHz and applied reverse voltage of 4.0 V D.C.

ÿ 2ÿ


Junction Capacitance (pF)
100
10
1
0.1
1.0
10
100
Reverse Voltage (V)